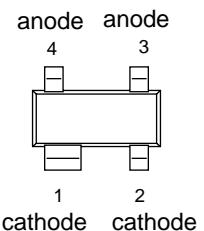
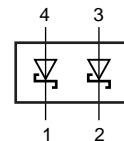




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## BAS40-07 Plastic-Encapsulate Transistors

SCHOTTKY BARRIER DIODE ARRAYS



### FEATURES

- Low Forward voltage drop
- Fast switching

Marking: 47

### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	$V_{RM}$	40	V
DC Blocking Voltage	$V_R$		
Average Rectified Output Current	$I_O$	200	mA
Power Dissipation	$P_d$	200	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Junction temperature	$T_J$	125	°C
Storage temperature range	$T_{STG}$	-65-125	°C

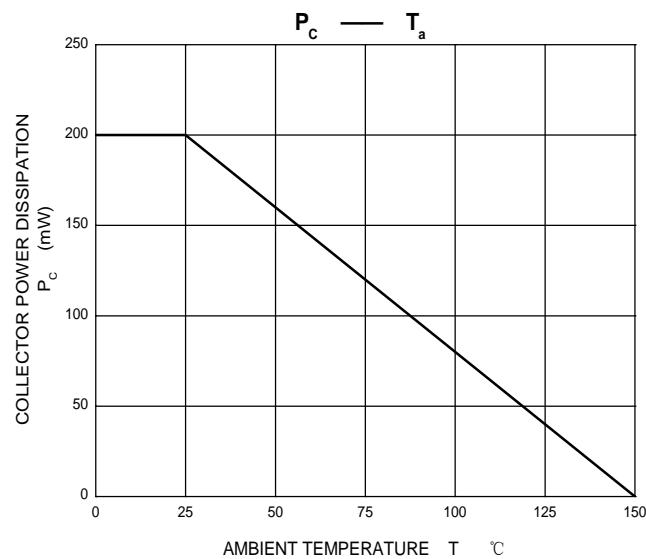
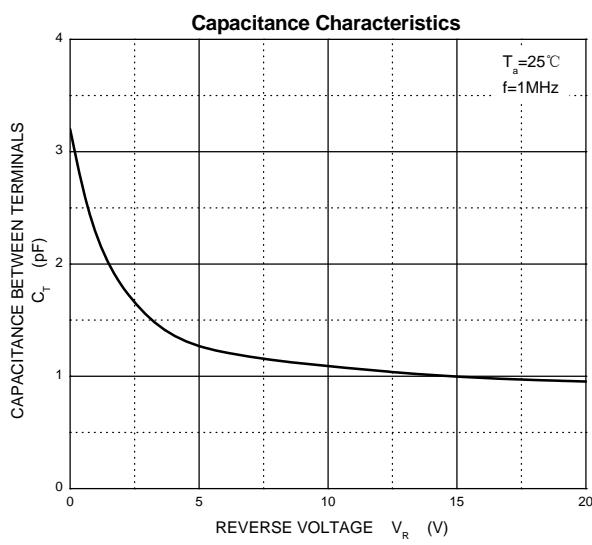
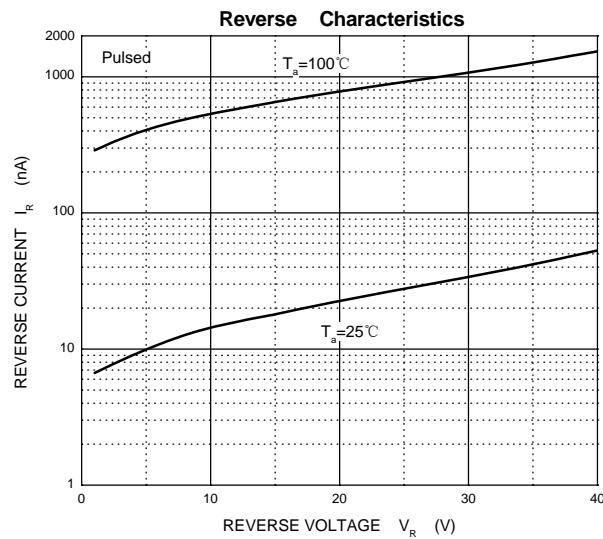
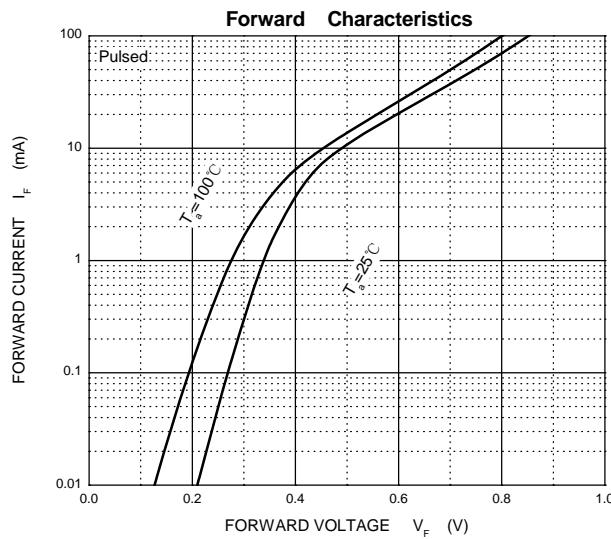
### Electrical Ratings @Ta=25°C

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	$I_R$	$V_R = 30V$		200	nA
Forward voltage	$V_F$	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Total capacitance	$C_T$	$V_R = 0, f = 1MHz$		5	pF
Reverse recovery time	$t_{rr}$	$I_F = 10mA, I_R = I_F = 1mA$ $R_L = 100\Omega$		5	ns



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## Typical Characteristics





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## Package Outline

Plastic surface mounted package

SOT-143

DIM <sup>N</sup>	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	—
B	.047	.055	1.20	1.40	—
C	.031	.047	.80	1.20	—
D	.014	.018	.37	.510	—
E	.030	.035	.76	.940	—
G	.076	BSC	1.92	BSC	—
H	.068	BSC	1.72	BSC	—
J	.003	.005	.085	.180	—
K	.002	.005	.013	.010	—
L	.010	.022	—	.55	REF
S	.082	.104	2.10	2.64	—